SQD40081EL

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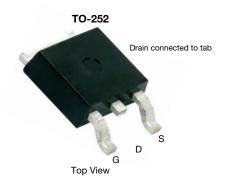
Vishay Siliconix

RoHS

COMPLIANT HALOGEN

FREE

Automotive P-Channel 40 V (D-S) 175 °C MOSFET

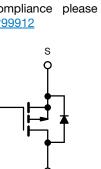


PRODUCT SUMMARY					
V _{DS} (V)	-40				
$R_{DS(on)}$ (Ω) at V_{GS} = -10 V	0.0085				
$R_{DS(on)} (\Omega)$ at $V_{GS} = -4.5 V$	0.0105				
I _D (A)	-50				
Configuration	Single				
Package	TO-252				

FEATURES

- TrenchFET® power MOSFET
- Package with low thermal resistance
- 100 % $R_{\rm q}$ and UIS tested
- AEC-Q101 qualified
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

GC



P-Channel MOSFET

D

ABSOLUTE MAXIMUM RATINGS ($T_C = 25 \degree C$, unless otherwise noted)					
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-source voltage		V _{DS}	-40	V	
Gate-source voltage	V _{GS}	± 20	v		
Continuous drain current ^a	T _C = 25 °C	I-	-50		
Continuous drain current ~	T _C = 125 °C	I _D	-38		
Continuous source current (diode conduction) ^a	I _S	-50	А		
Pulsed drain current ^b	I _{DM}	-200			
Single pulse avalanche current	L = 0.1 mH	I _{AS}	-35		
Single pulse avalanche energy		E _{AS}	61	mJ	
Maximum power dissipation ^b	T _C = 25 °C	Π_	71	w	
	T _C = 125 °C	P _D	23	٧V	
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175	С°	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount ^c	R _{thJA}	50	°C/W
Junction-to-case (drain)		R _{thJC}	2.1	0/10

Notes

a. Package limited

b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %

c. When mounted on 1" square PCB (FR4 material)

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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0 V, I_D = -250 \mu A$		-40	-	-	V
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_D = -250 \ \mu A$		-2.0	-2.5	V
Gate-source leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$		-	-	± 100	nA
		$V_{GS} = 0 V$	V _{DS} = -40 V	-	-	-1	μA
Zero gate voltage drain current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = -40 V, T _J = 125 °C	-	-	-50	
		$V_{GS} = 0 V$	V _{DS} = -40 V, T _J = 175 °C	-	-	-200	
On-state drain current ^a	I _{D(on)}	V _{GS} = -10 V	$V_{DS} \le -5 V$	-50	-	-	А
		V _{GS} = -10 V	I _D = -25 A	-	0.0070	0.0085	Ω
Durin an una state unaistance 3		V _{GS} = -10 V	I _D = -25 A, T _J = 125 °C	-	-	0.0110	
Drain-source on-state resistance ^a	R _{DS(on)}	$V_{GS} = -10 V$	I _D = -25 A, T _J = 175 °C	-	-	0.0131	
		V _{GS} = -4.5 V	I _D = -20 A	-	0.0086	0.0105	
Forward transconductance b	9 _{fs}	V _{DS} = -15 V, I _D = -25 A		-	92	-	S
Dynamic ^b		•			•		
Input capacitance	C _{iss}		V _{DS} = -25 V, f = 1 MHz	-	7365	9950	pF
Output capacitance	C _{oss}	$V_{GS} = 0 V$		-	576	800	
Reverse transfer capacitance	C _{rss}			-	548	750	
Total gate charge ^c	Qg			-	138	210	
Gate-source charge ^c	Q _{gs}	V _{GS} = -10 V	-10 V V _{DS} = -20 V, I _D = -50 A		21	-	nC
Gate-drain charge ^c	Q _{gd}			-	21	-	
Gate resistance	Rg	f = 1 MHz		1.5	3.15	4.8	Ω
Turn-on delay time ^c	t _{d(on)}			-	13	20	
Rise time ^c	tr	$\label{eq:VDD} \begin{array}{l} V_{DD} = -20 \mbox{ V}, \mbox{ R}_L = 0.4 \ \Omega \\ I_D \cong -50 \mbox{ A}, \mbox{ V}_{GEN} = -10 \mbox{ V}, \mbox{ R}_g = 1 \ \Omega \end{array}$		-	81	130	ns
Turn-off delay time ^c	t _{d(off)}			-	103	160	
Fall time ^c	t _f			-	153	250	
Source-Drain Diode Ratings and Chara	cteristics b	•					
Pulsed current ^a	I _{SM}			-	-	-200	А
Forward voltage	V _{SD}	I _F = -50 A, V _{GS} = 0 V		-	-0.96	-1.5	V
Body diode reverse recovery time	t _{rr}	I _F = -30 A, di/dt = 100 A/μs		-	56	120	ns
Body diode reverse recovery charge	Q _{rr}			-	83	170	nC
Reverse recovery fall time	ta			-	34	-	ns
neverse recovery fail time							
Reverse recovery rise time	t _b			-	22	-	115

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %

b. Guaranteed by design, not subject to production testing

c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

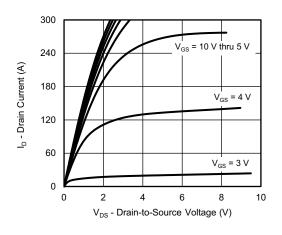
2



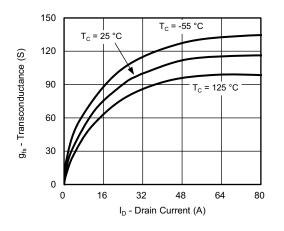
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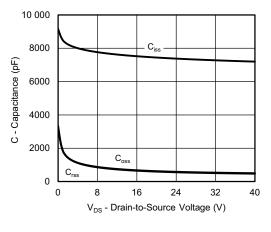
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



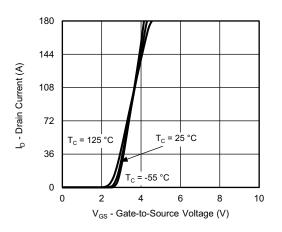
Output Characteristics



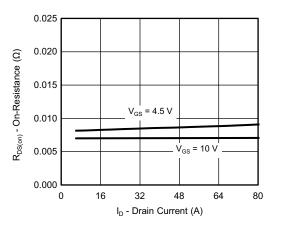
Transconductance



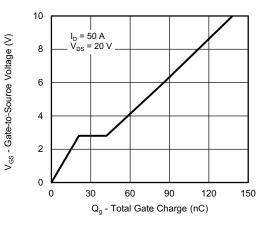
Capacitance



Transfer Characteristics



On-Resistance vs. Drain Current



Gate Charge

S17-1624-Rev. A, 23-Oct-17

3

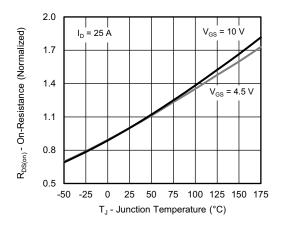
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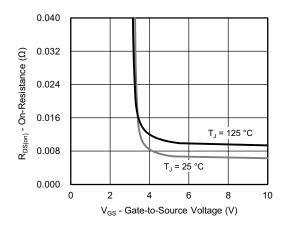


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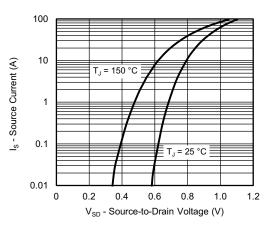
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



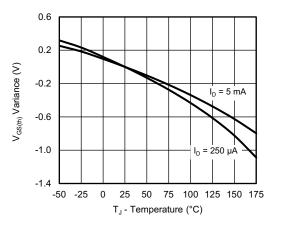
On-Resistance vs. Junction Temperature

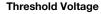


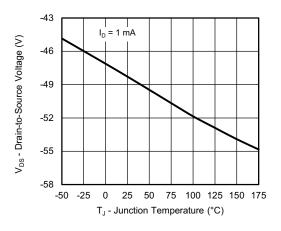
On-Resistance vs. Gate-to-Source Voltage



Source Drain Diode Forward Voltage







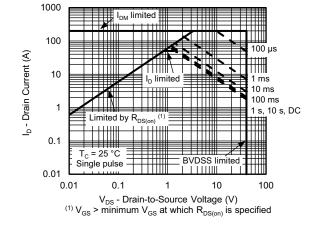
Drain Source Breakdown vs. Junction Temperature

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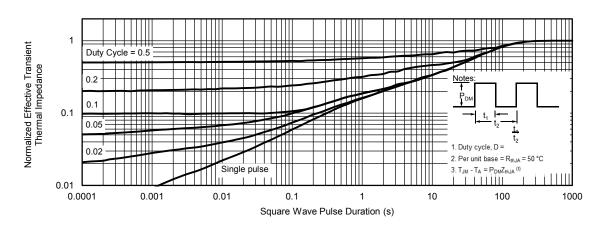
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THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)



Safe Operating Area



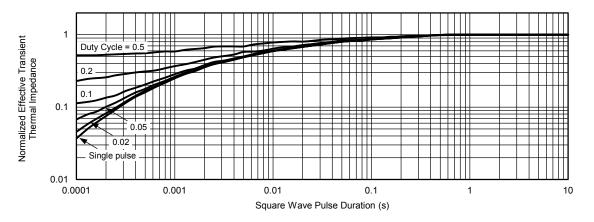
Normalized Thermal Transient Impedance, Junction-to-Ambient



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Document Number: 75677

THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

• The characteristics shown in the two graphs

S17-1624-Rev. A, 23-Oct-17

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?75677.

6





Е b3 Ľ Δ ŝ b2 e1 Б E1

C2 т gage plane height (0.5 mm)

-C

- A1

TO-252AA Case Outline

	MILLIN	IETERS	INCHES		
DIM.	MIN.	MAX.	MIN.	MAX.	
А	2.18	2.38	0.086	0.094	
A1	-	0.127	-	0.005	
b	0.64	0.88	0.025	0.035	
b2	0.76	1.14	0.030	0.045	
b3	4.95	5.46	0.195	0.215	
С	0.46	0.61	0.018	0.024	
C2	0.46	0.89	0.018	0.035	
D	5.97	6.22	0.235	0.245	
D1	4.10	-	0.161	-	
Е	6.35	6.73	0.250	0.265	
E1	4.32	-	0.170	-	
Н	9.40	10.41	0.370	0.410	
е	2.28	BSC	0.090 BSC		
e1	4.56	BSC	0.180 BSC		
L	1.40	1.78	0.055	0.070	
L3	0.89	1.27	0.035	0.050	
L4	-	1.02	-	0.040	
L5	1.01	1.52	0.040	0.060	
ECN: T13-0592-Rev. A, 02-Sep-13 DWG: 6019					

Note

• Dimension L3 is for reference only.





Vishay Siliconix

RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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